DMT10H072LFV-7 Datasheet

DiGi Electronics Part Number	DMT10H072LFV-7-DG
Manufacturer	Diodes Incorporated
Manufacturer Product Number	DMT10H072LFV-7
Description	MOSFET N-CH 100V PWRDI3333
Detailed Description	N-Channel 100 V 4.7A (Ta), 20A (Tc) 2W (Ta) Surface Mount PowerDI3333-8 (Type UX)

https://www.DiGi-Electronics.com

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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
DMT10H072LFV-7	Diodes Incorporated
Series:	Product Status:
-	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
100 V	4.7A (Ta), 20A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
6V, 10V	62mOhm @ 4.5A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
2.8V @ 250µA	4.5 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	228 pF @ 50 V
FET Feature:	Power Dissipation (Max):
-	2W (Ta)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
PowerDI3333-8 (Type UX)	8-PowerVDFN
Base Product Number:	
DMT10	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	

Lead-free Green

DMT10H072LFV

100V N-CHANNEL ENHANCEMENT MODE MOSFET
PowerDI3333-8

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_C = +25°C
100V	62mΩ @ V_{GS} = 10V	20A
	77mΩ @ V_{GS} = 6V	16A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Power Management Functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.

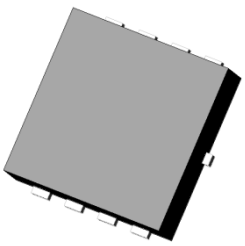
Features and Benefits

- Low $R_{DS(ON)}$ – Ensures On State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- Low On-Resistance
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

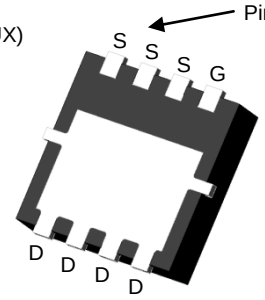
Mechanical Data

- Case: PowerDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.072 grams (Approximate)

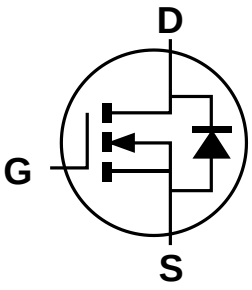
PowerDI3333-8 (Type UX)



Top View



Bottom View



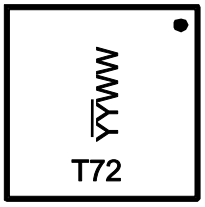
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Quantity per Reel
DMT10H072LFV-7	PowerDI3333-8 (Type UX)	2,000/Tape & Reel
DMT10H072LFV-13	PowerDI3333-8 (Type UX)	3,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds
4. For packaging details, go to our website athttps://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



T72= Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 19 = 2019)
WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.

DMT10H072LFV

Maximum Ratings (@T_A = +25°C unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	100	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current, V_{GS} = 10V (Note 5)	T_A = +25°C T_A = +70°C	I_D	4.7 3.7	A
Continuous Drain Current V_{GS} = 10V (Note 6)	T_C = +25°C T_C = +70°C	I_D	20 16	A
Pulsed Drain Current (10µs Pulse, T_C=+25°C, Package Limited)		I_{DM}	80	A
Pulsed Body Diode Current (10µs Pulse, T_C =+25°C, Package Limited)		I_{SM}	80	A
Maximum Body Diode Continuous Current		I_S	2	A
Avalanche Current (Note 9), L=0.1mH		I_{AS}	6	A
Avalanche Energy (Note 9), L=0.1mH		E_{AS}	1.8	mJ

Thermal Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	2	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	61	°C/W
Total Power Dissipation (Note 6)	P_D	37.8	W
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	3.3	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	100	-	-	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	-	-	1	µA	V_{DS} = 80V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	-	-	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.5	-	2.8	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	-	50.6	62	mΩ	V_{GS} = 10V, I_D = 4.5A
		-	61.2	77		V_{GS} = 6V, I_D = 4A
	$R_{DS(ON)}$	-	82.5	109	mΩ	V_{GS} = 4.5V, I_D = 2.7A
Diode Forward Voltage	V_{SD}	-	0.76	1	V	V_{GS} = 0V, I_S = 1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	-	228	-	pF	V_{DS} = 50V, V_{GS} = 0V, f = 1MHz
Output Capacitance	C_{oss}	-	89.3	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	2.5	-	pF	
Gate Resistance	R_g	-	8.2	-	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	-	2.5	-	nC	V_{DS} = 50V, I_D = 4.5A
Total Gate Charge (V_{GS} = 10V)	Q_g	-	4.5	-	nC	
Gate-Source Charge	Q_{gs}	-	0.6	-	nC	
Gate-Drain Charge	Q_{gd}	-	1.3	-	nC	
Turn-On Delay Time	$t_{D(ON)}$	-	3.0	-	ns	V_{DS} = 50V, R_L = 11Ω V_{GS} = 10V, R_{GEN} = 3Ω
Turn-On Rise Time	t_R	-	3.1	-	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	-	12.3	-	ns	
Turn-Off Fall Time	t_F	-	4.3	-	ns	
Reverse Recovery Time	t_{RR}	-	22.9	-	ns	I_F = 4.5A, di/dt = 300A/µs
Reverse Recovery Charge	Q_{RR}	-	45.2	-	nC	

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
6. Thermal resistance from junction to soldering point (on the exposed drain pad).
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.
9. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.

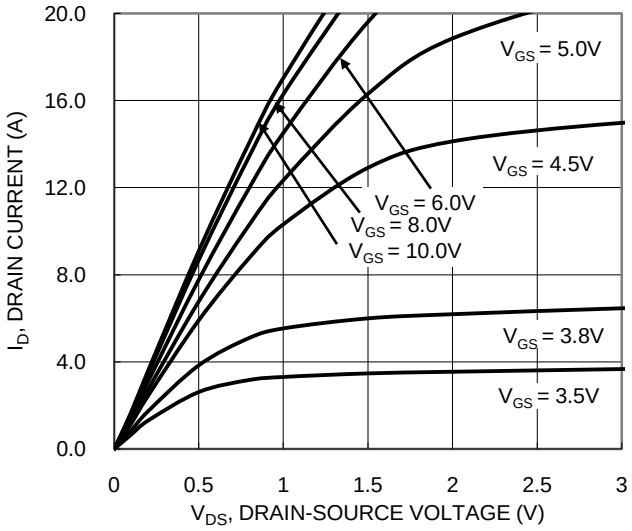


Figure 1. Typical Output Characteristic

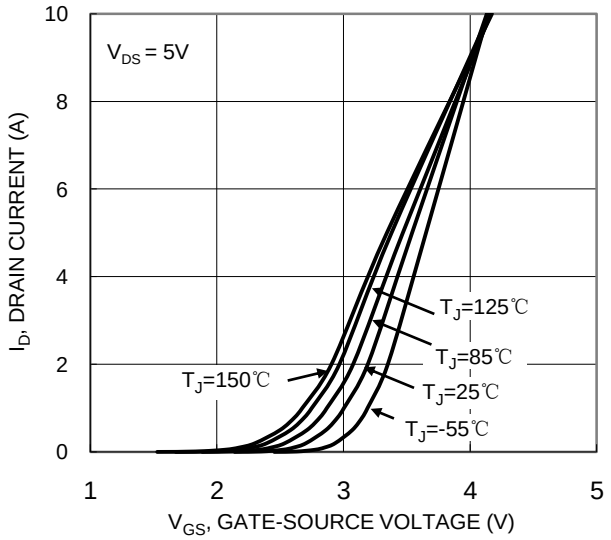


Figure 2. Typical Transfer Characteristic

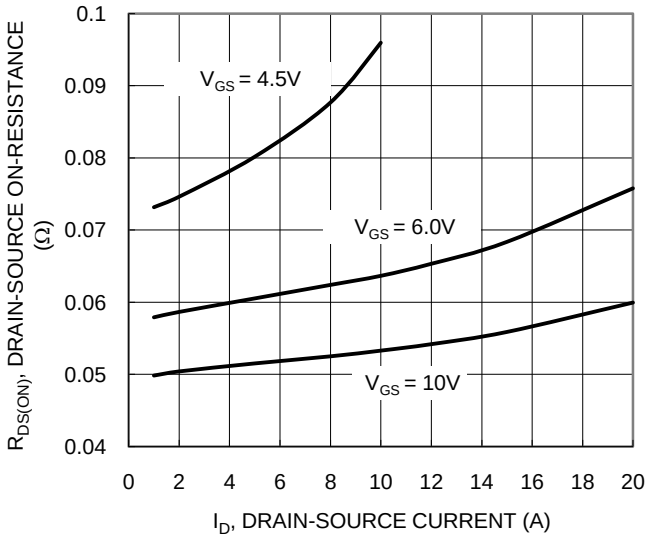


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

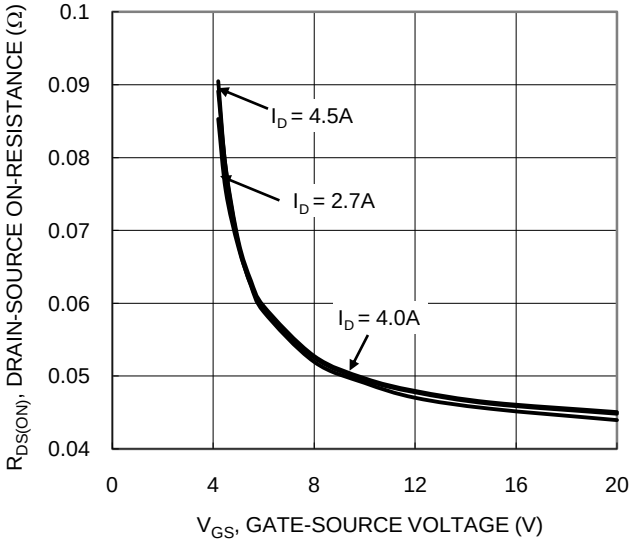


Figure 4. Typical Transfer Characteristic

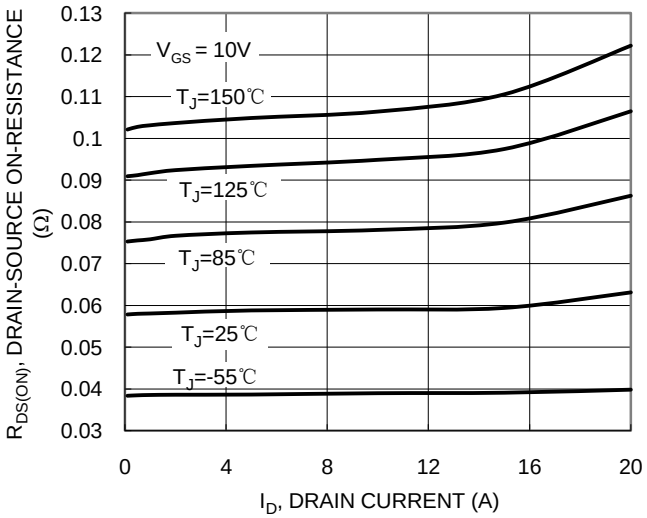


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

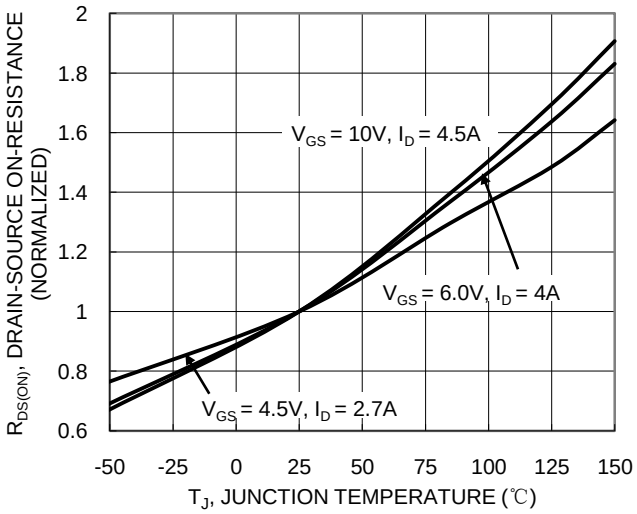


Figure 6. On-Resistance Variation with Junction Temperature

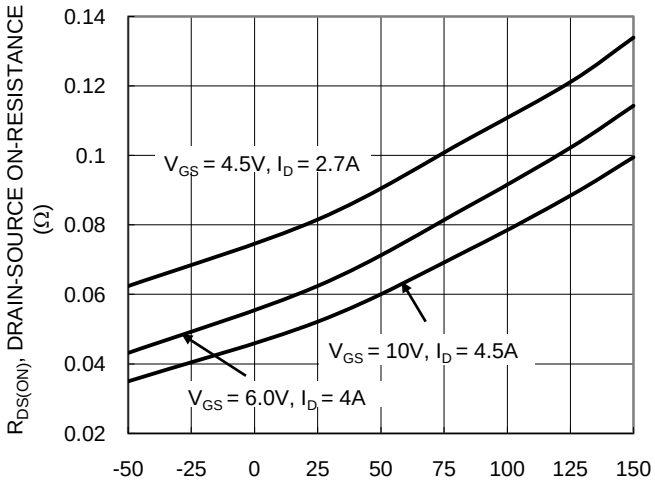


Figure 7. On-Resistance Variation with Junction Temperature

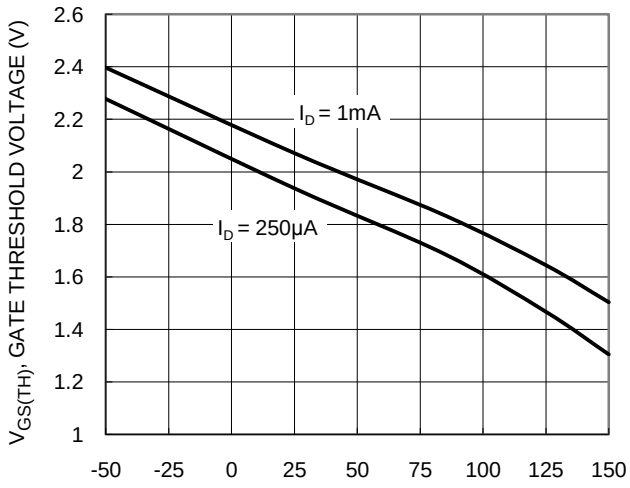


Figure 8. Gate Threshold Variation vs. Junction Temperature

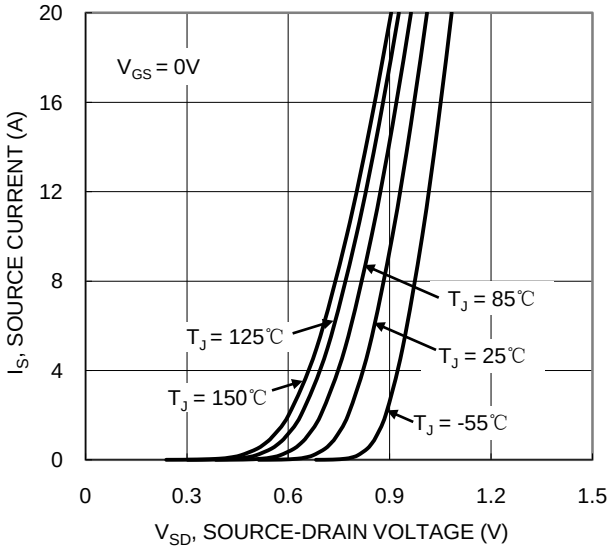


Figure 9. Diode Forward Voltage vs. Current

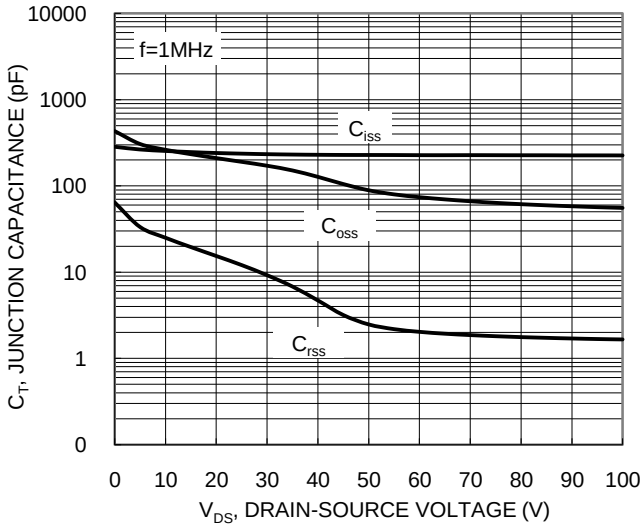


Figure 10. Typical Junction Capacitance

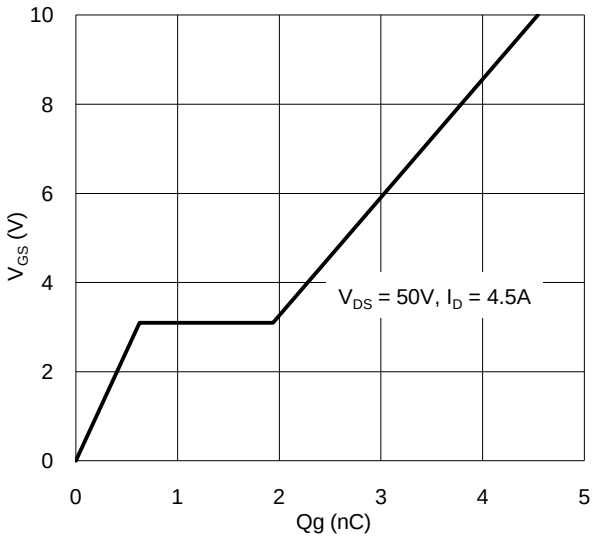


Figure 11. Gate Charge

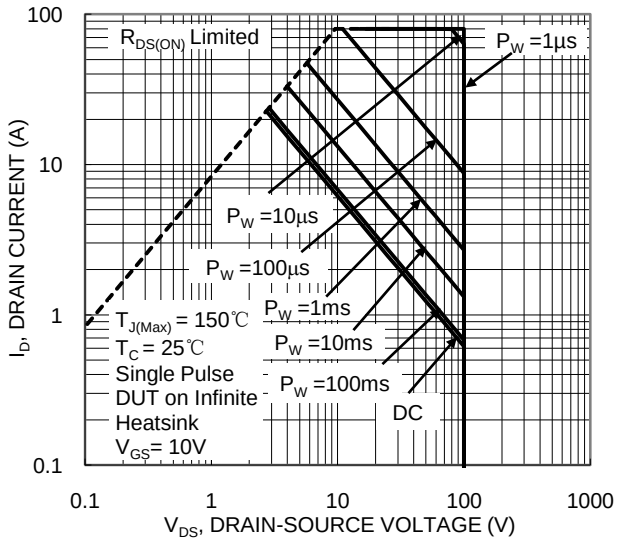


Figure 12. SOA, Safe Operation Area

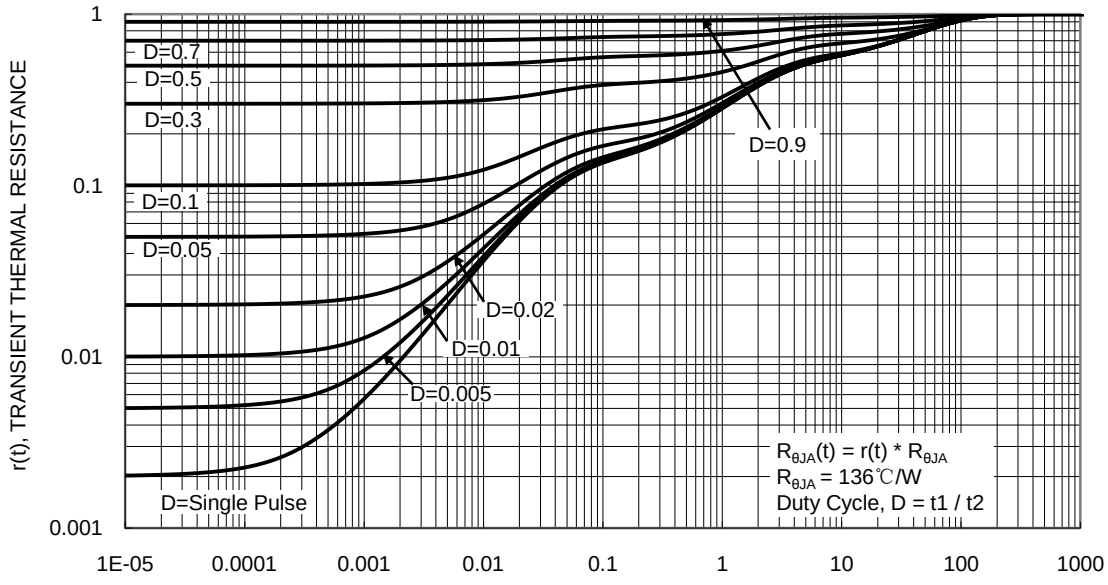
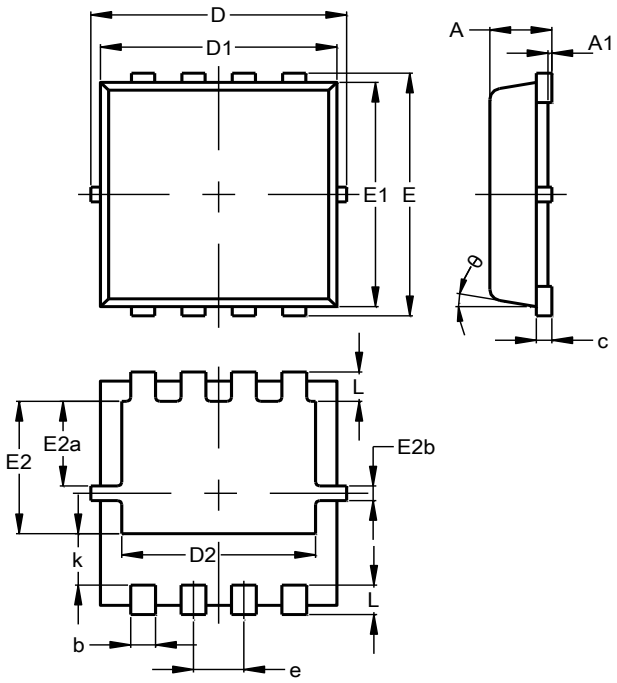


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)

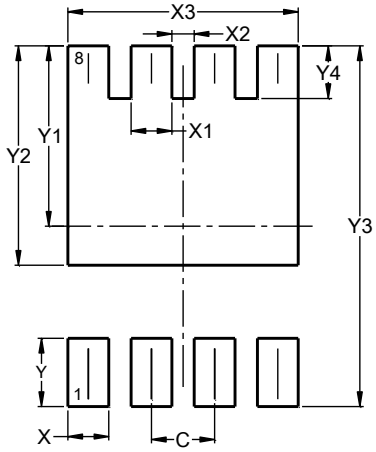


PowerDI3333-8 (Type UX)			
Dim	**Min**	**Max**	**Typ**
A	0.75	0.85	0.80
A1	0.00	0.05	--
b	0.25	0.40	0.32
c	0.10	0.25	0.15
D	3.20	3.40	3.30
D1	2.95	3.15	3.05
D2	2.30	2.70	2.50
E	3.20	3.40	3.30
E1	2.95	3.15	3.05
E2	1.60	2.00	1.80
E2a	0.95	1.35	1.15
E2b	0.10	0.30	0.20
e	0.65 BSC		
k	0.50	0.90	0.70
L	0.30	0.50	0.40
θ	0°	12°	10°
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540

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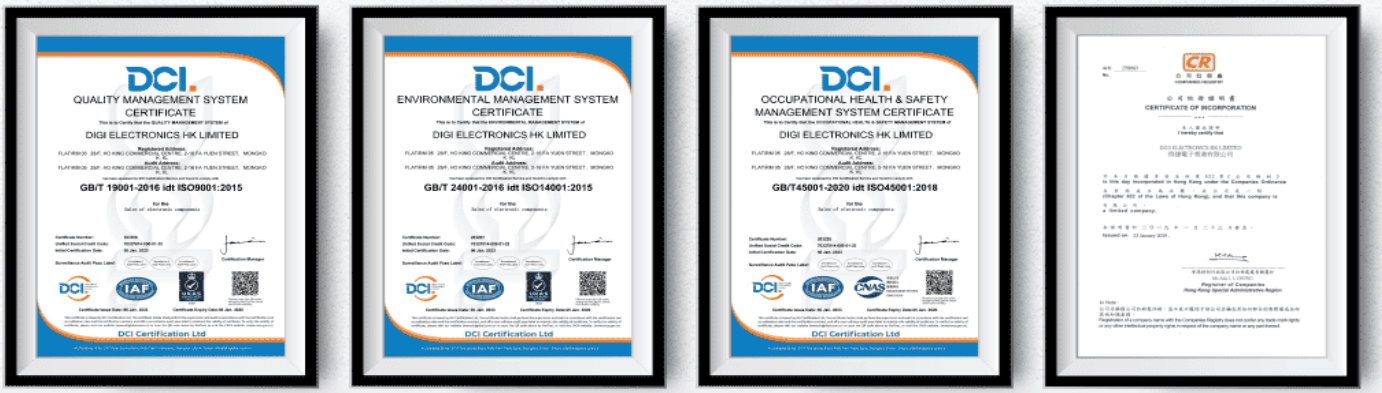

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